

PATENT ABSTRACTS OF JAPAN

(11)Publication number : **07-014767**
 (43)Date of publication of application : **17.01.1995**

(51)Int.Cl. **H01L 21/203**
H01L 21/20

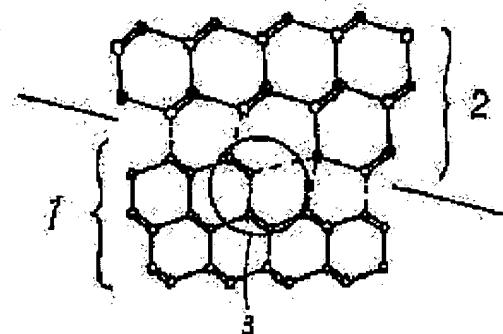
(21)Application number : **05-152041** (71)Applicant : **NEC CORP**
 (22)Date of filing : **23.06.1993** (72)Inventor : **KAWANO MASAYA**

(54) METHOD FOR GROWING CDTE ON SI SUBSTRATE BY MBE

(57)Abstract:

PURPOSE: To provide a method for growing CdTe epitaxial layer stably on an Si substrate by MBE.

CONSTITUTION: A Si (221) off substrate (3° off in the direction [-1 -1 4]) is employed for growing CdTe. In the substrate, lattice irregularity becomes 0 in the direction normal to step 3 because of the lattice relaxation. The substrate is cleaned at first by RCA cleaning before it is introduced to a growth system. The substrate is heated up to about 850°C in a preheat chamber where protective oxide is removed from the surface of the substrate before it is introduced into a growth chamber. Temperature of the substrate is set at a predetermined level in the growth chamber and a molecular beam of CdTe is projected to effect the growth. At first, CdTe is grown by 500Å at 200°C of substrate temperature and then it is annealed at 400°C for 10min without irradiating the molecular beam before CdTe is grown again at 300°C of substrate temperature thus obtaining a CdTe (112) off epitaxial layer 2. Half width of 220sec is obtained in X-ray diffraction. It is a very good value for CdTe/Si.



LEGAL STATUS

[Date of request for examination] **24.06.1993**

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] **2513126**

[Date of registration] **30.04.1996**

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]

30.04.2001